

Zhiting Lin

List of Publications by Year in descending order

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12
papers

382
citations

1163117

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1199594

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12
docs citations

12
times ranked

572
citing authors

#	ARTICLE	IF	CITATIONS
1	Growth mechanisms of GaN epitaxial films grown on ex situ low-temperature AlN templates on Si substrates by the combination methods of PLD and MOCVD. Journal of Alloys and Compounds, 2017, 718, 28-35.	5.5	8
2	Employing Al buffer layer with Al droplets-distributed surface to obtain high-quality and stress-free GaN epitaxial films on Si substrates. Journal of Materials Science, 2017, 52, 1318-1329.	3.7	6
3	Achieving High-Performance Blue GaN-Based Light-Emitting Diodes by Energy Band Modification on Al _x In _{1-x} Ga _{1-2x} N _{2x} GaN-Based Light-Emitting Diodes by Energy Band Modification on Al _x In _{1-x} Ga _{1-2x} N _{2x} Electron Blocking Layer. IEEE Transactions on Electron Devices, 2017, 64, 472-480.	3.0	6
4	Stress management on underlying GaN-based epitaxial films: A new vision for achieving high-performance LEDs on Si substrates. Journal of Applied Physics, 2017, 122, 204503.	2.5	4
5	High-Performance GaN-Based LEDs on Si Substrates: The Utility of Ex Situ Low-Temperature AlN Template With Optimal Thickness. IEEE Transactions on Electron Devices, 2017, 64, 4540-4546.	3.0	6
6	GaN-based light-emitting diodes on various substrates: a critical review. Reports on Progress in Physics, 2016, 79, 056501.	20.1	236
7	Effect of residual stress on the microstructure of GaN epitaxial films grown by pulsed laser deposition. Applied Surface Science, 2016, 369, 414-421.	6.1	16
8	Growth evolution of AlN films on silicon (111) substrates by pulsed laser deposition. Journal of Applied Physics, 2015, 117, .	2.5	21
9	Performance improvement of GaN-based light-emitting diodes grown on Si(111) substrates by controlling the reactor pressure for the GaN nucleation layer growth. Journal of Materials Chemistry C, 2015, 3, 1484-1490.	5.5	31
10	Effect of InGaAs interlayer on the properties of GaAs grown on Si (111) substrate by molecular beam epitaxy. Journal of Applied Physics, 2014, 116, 193508.	2.5	12
11	Nitridation effect of the Al ₂ O ₃ substrates on the quality of the GaN films grown by pulsed laser deposition. RSC Advances, 2014, 4, 39651-39656.	3.6	14
12	Epitaxial growth of high-quality AlN films on metallic nickel substrates by pulsed laser deposition. RSC Advances, 2014, 4, 27399-27403.	3.6	11